

INFORMATION DISCLOSURE S C I T A T I O N U. S. P A T E N T & T R A D E M A R K O F F I C E JUN 7 5 2004 (Use several sheets if necessary)		ATTY. DOCKET NO.	SERIAL NO.			
		1035-501 APPLICANT	10/802,735			
		TAKAFUJI et al FILING DATE	GROUP			
		March 18, 2004	2811			
U. S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS SUBCLASS		
FILING DATE IF APPROPRIATE						
FOREIGN PATENT DOCUMENTS						
				TRANSLATION		
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
TT	8-262474 A	10-1996	JP	—	—	partial
TT	7-235651 A	9-1995	JP	—	—	partial
TT	93/15589 A1	8-1993	WO	—	—	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, etc.)						
TT	Salerno et al, "Single Crystal Silicon AMLCDs", Conference Record of the 1994 International Display Research Conference (IDRC) (1994), pp. 39-44					
TT	Tong et al, "Semiconductor Wafer Bonding: Science and Technology", John Wiley & Sons, Inc., New York, 1999, pp. 8-11, 48-55, 58-65, 108 and 109					
TT	Warner et al, "Low-Temperature Oxide-Bonded Three-Dimensional Integrated Circuits", 2002 IEEE International SOI Conference, October 2002, pp. 123-125					
TT	Allen et al, "SOI Uniformity and Surface Smoothness Improvement Using GCIB Processing", 2002 IEEE International SOI Conference, October 2002, pp. 192-193					
TT	Matsumoto et al, "70 nm SOI-CMOS of 135 GHz f_{max} with Dual Offset-Implanted Source-Drain Extension Structure for RF/Analog and Logic Applications", International Electron Device Meeting, December 2001, pp. 219-222					
TT	Vandooren et al, "Scaling Assessment of Fully-Depleted SOI Technology at the 30nm Gate Length Generation", 2002 IEEE International SOI Conference Proceedings, October 2002, pp. 25-27					
*Examiner		11/11/2004	Date Considered	12/01/2004		

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)